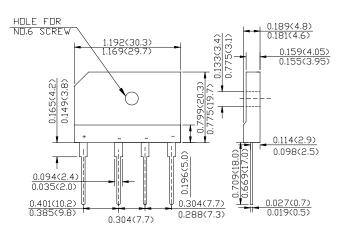


SILICON BRIDGE RECTIFIERS GLASS PASSIVATED BRIDGE RECTIFIERS GBJ/KBJ1001 thru GB /KBJ1007 50 to 1000 V 10.0 A

FEATURES

- Rating to 1000V PRV
- Ideal for printed circuit board
- Low forward voltage drop, high current capability
- Reliable low cost construction utilizing Molded plastic technique results in Inexpensive product
- The plastic material has UL Flammability classification 94V-O



GBJ/KBJ

Maximum Ratings and Electrical Characteristics

Ratings at 25° C ambient temperature unless otherwise specified. Single phase , half wave, 60HZ, resistive or inductive load. For capacitive load, derate current by 20%.

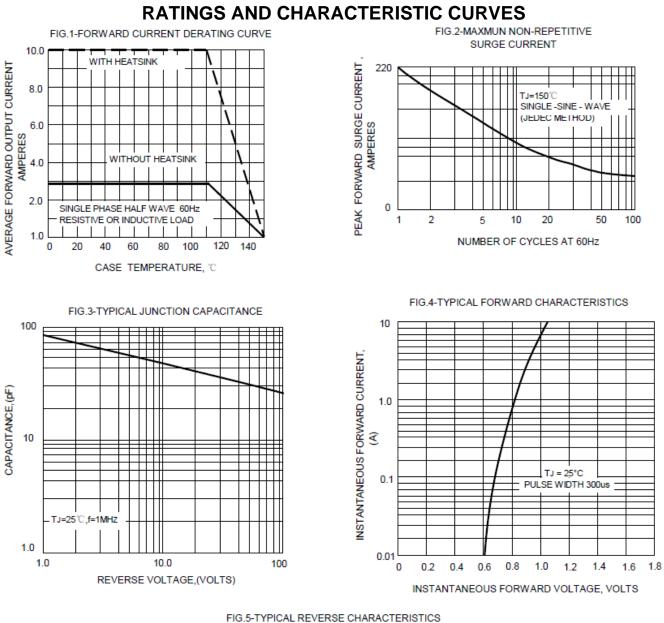
CHARACTERISTICS	SYMBOL	GBJ KBJ 1001	GBJ KBJ 1002	GBJ KBJ 1003	GBJ KBJ 1004	GBJ KBJ 1005	GBJ KBJ 1006	GBJ KBJ 1007	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward (with heatsink Note2) Rectified Current @ $T_C = 110^{\circ}C$ (without heatsink)	V _(AV)	10.0 3							Amp
Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load	IFSM	200							Amp
Maximum DC Forward Voltage at 5.0A DC	V_{F}	1.05							Volts
$\begin{array}{llllllllllllllllllllllllllllllllllll$	Ι _R	5.0 500							uAmp
I ² t Rating for fusing (t<8.3ms)	I ² T	120							A ² S
Typical Junction Capacitance (Note 1)	CJ	55							pF
Typical Thermal Resistance	R₀Jc	1.4							°C/W
Operating Temperature Range	TJ	-55 to +150							°C
Storage Temperature Range	T _{STG}	-55 to +150							°C

Notes:

- 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
- 2. Device mounted on 150mm x 150mm X 1.6mm Cu Plate Heatsink.



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1000 INSTANTANEOUS REVERSE CURRENT ,(uA) TJ=125 100 TJ=100 10 TJ=50°C 1.0 TJ=25" 0.1 20 0 40 60 80 100

PERCENT OF RATED PEAK REVERSE VOLTAGE,(%)